ABSTRACT

A method of manufacturing a semiconductor device in which is provided a substrate 12 on which an interconnect pattern 10 is formed and which is covered by a protective layer 50 except a region of electrical connection with electrodes 22 of a semiconductor chip 20, the method comprising: a first step of providing an anisotropic conductive material 16 on the substrate 12 from a region of mounting of the semiconductor chip 20 to the protective layer 50, between the interconnect pattern 10 and the electrodes 22; and a second step of adhering the substrate 12 to the semiconductor chip 20 by means of the anisotropic conductive material 16 to electrically connect the interconnect pattern 10 with the electrodes 22.

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